What is claimed is:

1. A method comprising:

forming a dielectric layer on a substrate;

forming a metal interconnect in an opening in the dielectric layer; and

treating the dielectric layer with a solvent in a sonication bath to form pores in the dielectric layer.

2. The method of claim 1 wherein forming a metal interconnect in an opening in the dielectric layer comprises forming a dual damascene metal interconnect.

3. The method of claim 1 wherein treating the dielectric layer with a solvent in a sonication bath comprises immersing the substrate in a solvent.

4. The method of claim 1 wherein forming a metal interconnect in an opening in the dielectric layer comprises forming smooth sidewalls on the metal interconnect.

5. The method of claim 1 further comprising forming a capping layer over the dielectric layer.

6. The method of claim 1 wherein treating the dielectric layer with a solvent in a sonication bath

comprises providing sonic energy to the sonication bath in a frequency range of about 10 kilohertz to about 2000 kilohertz.

7. The method of claim 1 wherein the dielectric layer includes a porogen having a thermal stability greater than about 400 degrees C.

8. The method of claim 7 wherein the porogen comprises poly(vinyl alcohol).

9. The method of claim 7 wherein the porogen comprises polycarbonate.

10. A method comprising:

forming a metal interconnect in a dielectric material on a semiconductor substrate; and

directing an electron beam at the dielectric material to form pores in the dielectric material.

11. The method of claim 10 wherein directing the electron beam at the dielectric material comprises exposing at least most of the dielectric material to an electron beam flood.

12. The method of claim 10 wherein directing the electron beam at the dielectric material comprises scanning the electron beam across the dielectric material.

13. The method of claim 10 wherein directing an electron beam at the dielectric material further comprises fragmenting some of the dielectric material.

14. The method of claim 10 further comprising forming the dielectric material on the semiconductor substrate, the dielectric material having a pore-generating material therein with a thermal stability greater than about 400 degrees C.

15. The method of claim 14 wherein the pore-generating material comprises poly(methyl methacrylate).

16. A device comprising:

a semiconductor substrate having at least one layer with conductive metal lines thereon;

a dielectric material between the metal lines, the conductive metal lines having smooth sidewalls adjacent the dielectric material.

17. The device of claim 16 wherein the dielectric material is at least 50% porous.

18. The device of claim 16 wherein the dielectric material is over a conductive layer.

19. The device of claim 16 wherein the dielectric material comprises a carbon-doped oxide.

20. The device of claim 16 wherein the dielectric material has a dielectric constant below about 3.0.

21. The device of claim 16 wherein the dielectric material comprises fluorinated silica glass.

22. The device of claim 16 wherein the dielectric material is a silsesquioxane-based material.

23. The device of claim 16 wherein the dielectric material has a thermal stability greater than about 400 degrees C.